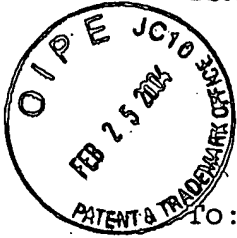


TSMC-03-395



February 18, 2004

To: Commissioner for Patents  
P.O.Box 1450  
Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572  
28 Davis Avenue  
Poughkeepsie, N.Y. 12603

Subject: | Serial No. 10/728,215 12/04/03 |

Yi-Lung Cheng et al.

NOVEL METHOD TO DEPOSIT CARBON  
DOPED SiO<sub>2</sub> FILMS WITH IMPROVED  
FILM QUALITY

#### INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation  
In An Application.

The following Patents and/or Publications are submitted to  
comply with the duty of disclosure under CFR 1.97-1.99 and  
37 CFR 1.56.

#### CERTIFICATE OF MAILING

I hereby certify that this correspondence is being  
deposited with the United States Postal Service as first class  
mail in an envelope addressed to: Commissioner for Patents,  
P.O. Box 1450, Alexandria, VA 22313-1450, on February 23, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

 2/23/04

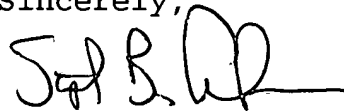
U.S. Patent Application Publication US 2003/0032292 A1 to Noguchi, "Fabrication Method of Semiconductor Integrated Circuit Device," discusses a Black Diamond film formed by a process involving trimethylsilane and oxygen.

U.S. Patent 6,372,632 to Yu et al., "Method to Eliminate Dishing of Copper Interconnects by the Use of a Sacrificial Oxide Layer," describes an organosilane such as trimethylsilane and a compensatory gas including Ar, O<sub>2</sub>, CH<sub>4</sub>, N<sub>2</sub>O, N<sub>2</sub>, H<sub>2</sub>, etc, employed to deposit a low k dielectric layer.

U.S. Patent 6,312,793 to Grill et al., "Multiphase Low Dielectric Constant Material," describes a dual phase dielectric layer in which a first phase is comprised of SiCOH.

U.S. Patent 6,541,397 to Bencher, "Removable Amorphous Carbon CMP Stop," discusses a siliconoxycarbide layer deposited with one or more organosilicon compounds, an oxidizing gas, and an inert gas at 50-5000 sccm.

Sincerely,

A handwritten signature in black ink, appearing to read "Stephen B. Ackerman".

Stephen B. Ackerman,  
Reg. No. 37761

Form PTO-1449

## INFORMATION DISCLOSURE CITATION IN AN APPLICATION

(Use several sheets if necessary)

Docket Number (Optional)

TSMC-03-395

Agreement Number

10 | 728,215

significant

Yi-Lung Cheng et al.

Filing Date

12/04/03

Group Meeting

## U. S. PATENT DOCUMENTS

[illegible]

## FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Portion, Pages, Etc.)

-	US Patent App. Pub. US 2003/0032292 A1 to Noguchi, Pub. Date 02/13/03, filed 7/19/02, US Class 438/692.

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.